

FCH20N60 / FCA20N60

600V N-Channel MOSFET

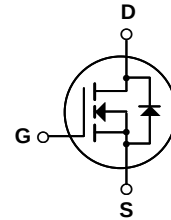
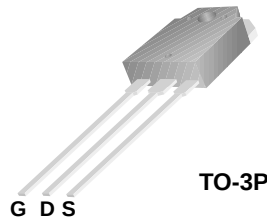
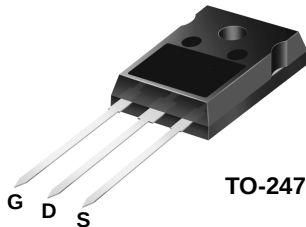
Features

- 650V @T_J = 150°C
- Typ. R_{DS(on)} = 0.15Ω
- Ultra low gate charge (typ. Q_g = 75nC)
- Low effective output capacitance (typ. C_{oss-eff} = 165pF)
- 100% avalanche tested

Description

SuperFET™ is, Fairchild's proprietary, new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.



Absolute Maximum Ratings

Symbol	Parameter	FCH20N60	FCA20N60	Unit
V _{DSS}	Drain-Source Voltage	600		V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	20 12.5		A A
I _{DM}	Drain Current - Pulsed (Note 1)	60		A
V _{GSS}	Gate-Source voltage	± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	690		mJ
I _{AR}	Avalanche Current (Note 1)	20		A
E _{AR}	Repetitive Avalanche Energy (Note 1)	20.8		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	208 1.67		W W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	--	0.6	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink	0.24	--	
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	41.7	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCH20N60	FCH20N60	TO-247	-	-	30
FCA20N60	FCA20N60	TO-3P	-	-	30

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA, T _J = 25°C	600	--	--	V
		V _{GS} = 0V, I _D = 250μA, T _J = 150°C	--	650	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	--	0.6	--	V/°C
BV _{DS}	Drain-Source Avalanche Breakdown Voltage	V _{GS} = 0V, I _D = 20A	--	700	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600V, V _{GS} = 0V	--	--	1	μA
		V _{DS} = 480V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 10A	--	0.15	0.19	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 10A (Note 4)	--	17	--	S
Dynamic Characteristics						
C _{iSS}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	--	2370	3080	pF
C _{oSS}	Output Capacitance		--	1280	1665	pF
C _{rSS}	Reverse Transfer Capacitance		--	95	--	pF
C _{oSS}	Output Capacitance	V _{DS} = 480V, V _{GS} = 0V, f = 1.0MHz	--	65	85	pF
C _{oSS} eff.	Effective Output Capacitance	V _{DS} = 0V to 400V, V _{GS} = 0V	--	165	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 300V, I _D = 20A R _G = 25Ω (Note 4, 5)	--	62	135	ns
t _r	Turn-On Rise Time		--	140	290	ns
t _{d(off)}	Turn-Off Delay Time		--	230	470	ns
t _f	Turn-Off Fall Time		--	65	140	ns
Q _g	Total Gate Charge	V _{DS} = 480V, I _D = 20A V _{GS} = 10V (Note 4, 5)	--	75	98	nC
Q _{gs}	Gate-Source Charge		--	13.5	18	nC
Q _{gd}	Gate-Drain Charge		--	36	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	20	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	60	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 20A dI _F /dt = 100A/μs (Note 4)	--	530	--	ns
Q _{rr}	Reverse Recovery Charge		--	10.5	--	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS} = 20A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 20A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

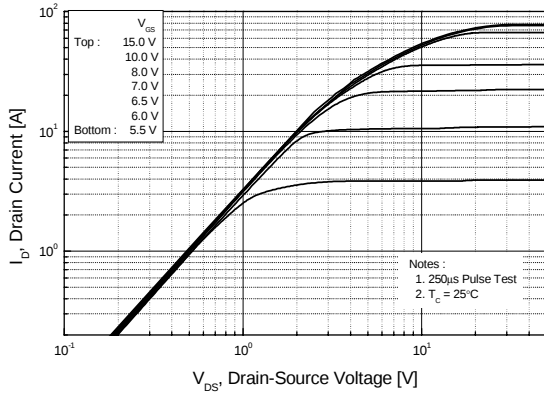


Figure 2. Transfer Characteristics

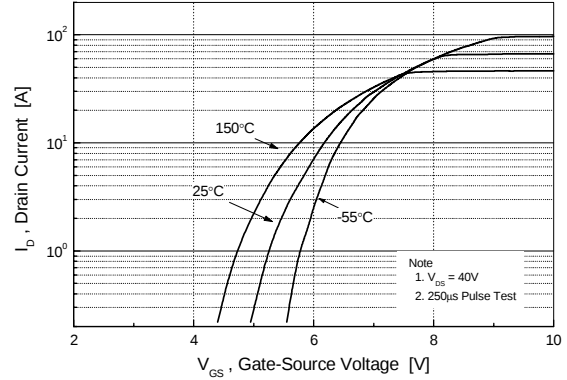


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

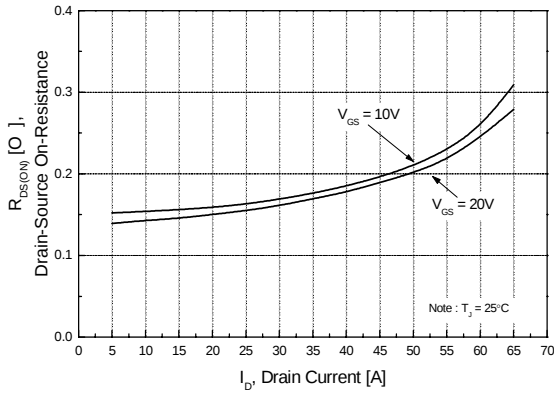


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

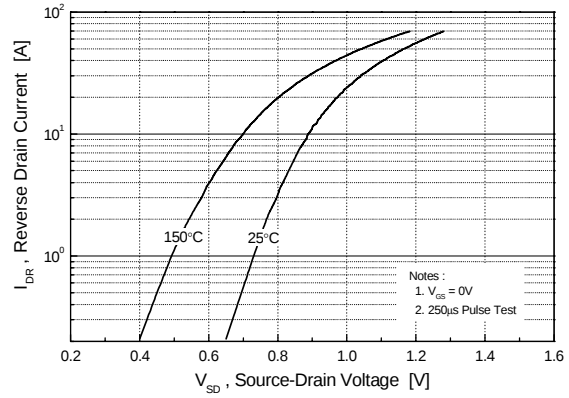


Figure 5. Capacitance Characteristics

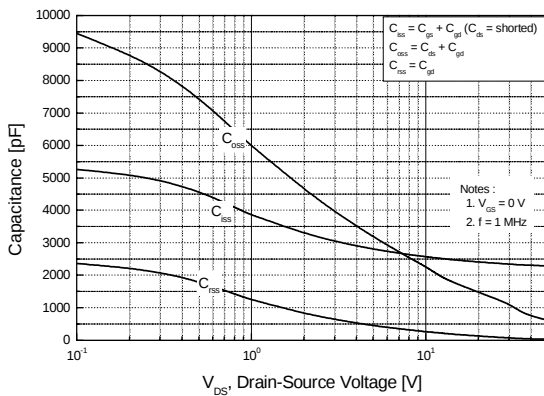
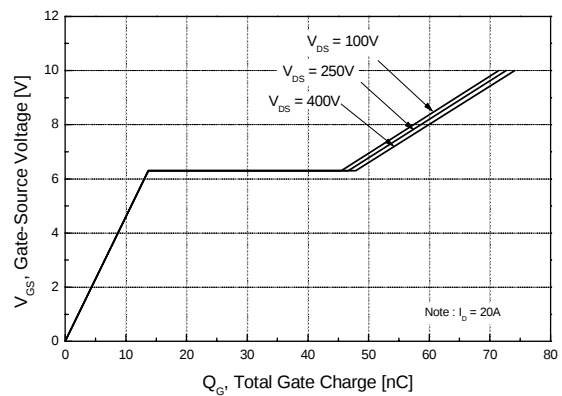


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

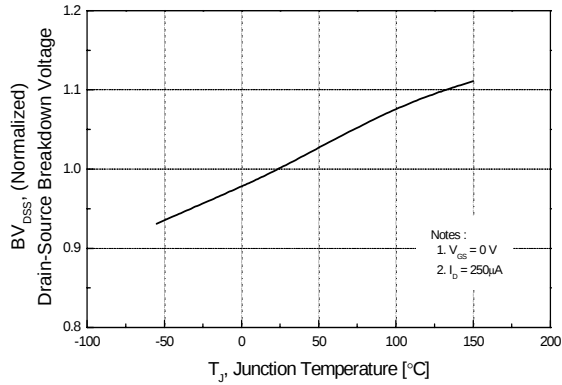


Figure 8. On-Resistance Variation vs. Temperature

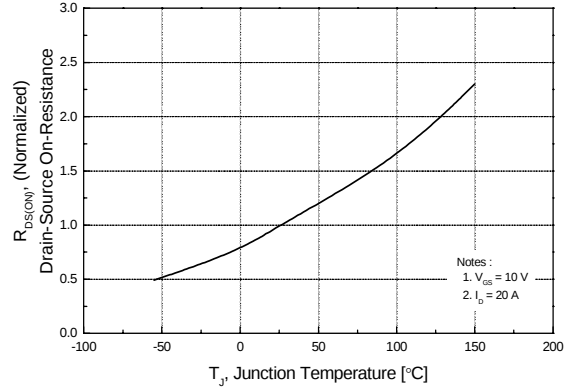


Figure 9. Maximum Safe Operating Area

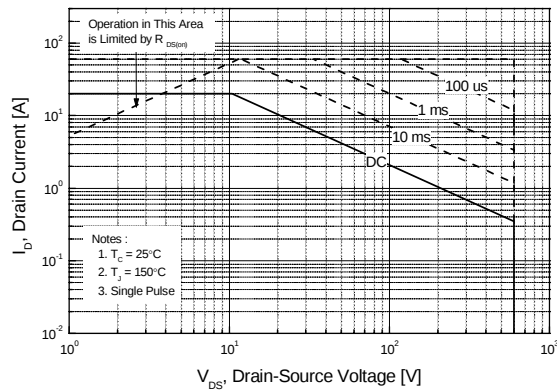


Figure 10. Maximum Drain Current vs. Case Temperature

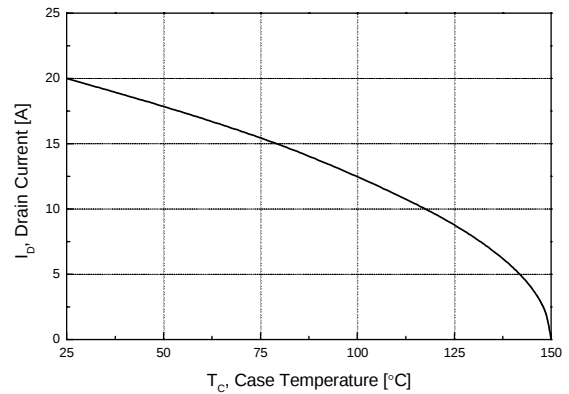
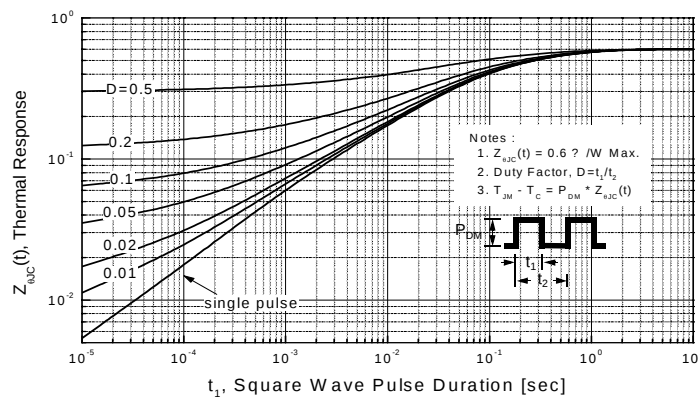
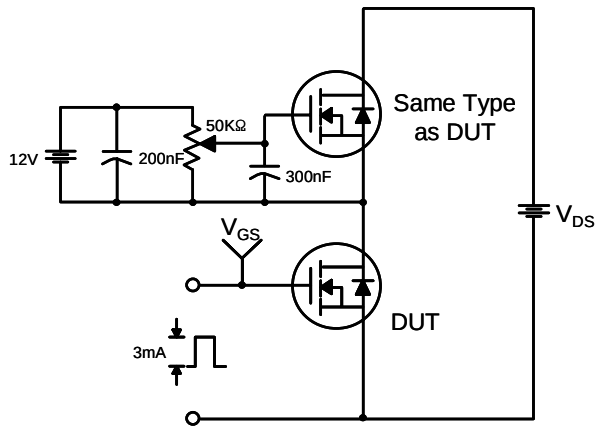


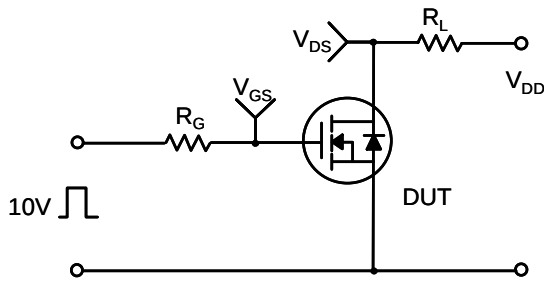
Figure 11. Transient Thermal Response Curve



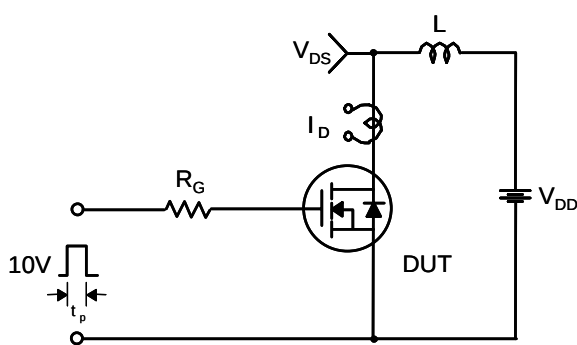
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

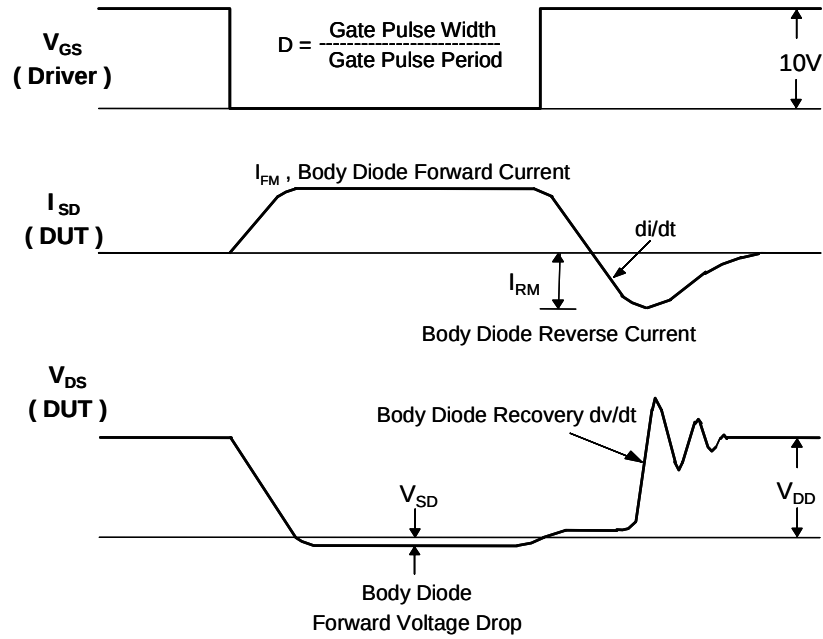
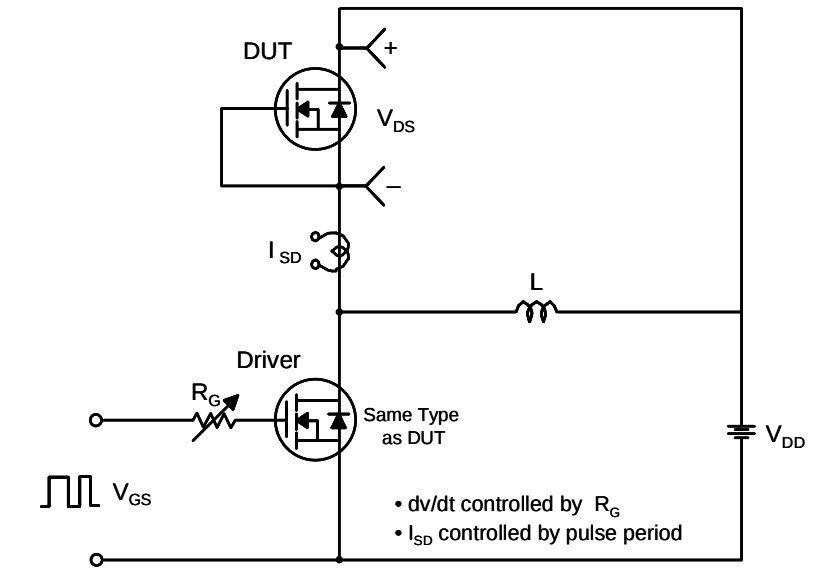


Unclamped Inductive Switching Test Circuit & Waveforms



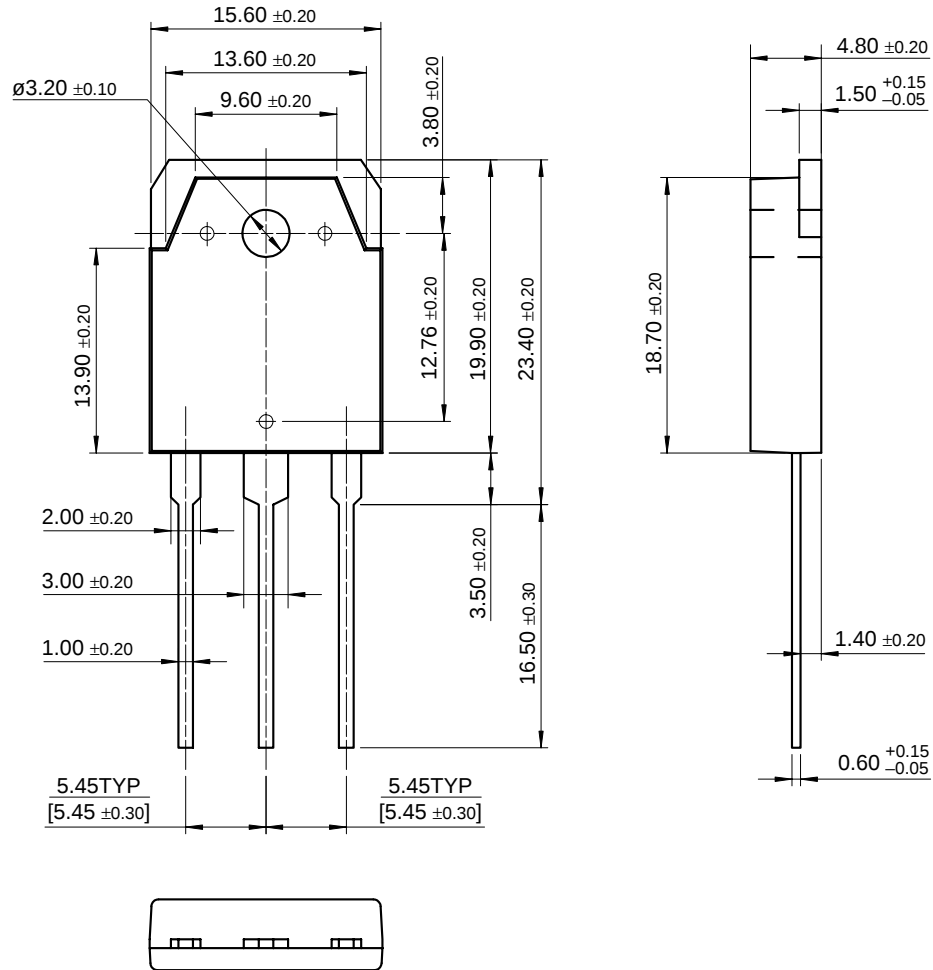
$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions (Continued)

TO-3P



Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE [™]	FAST [®]	IntelliMAX [™]	POP [™]	SPM [™]
ActiveArray [™]	FAST [™]	ISOPLANAR [™]	Power247 [™]	Stealth [™]
Bottomless [™]	FPS [™]	LittleFET [™]	PowerEdge [™]	SuperFET [™]
CoolFET [™]	FRFET [™]	MICROCOUPLER [™]	PowerSaver [™]	SuperSOT [™] -3
CROSSVOLT [™]	GlobalOptoisolator [™]	MicroFET [™]	PowerTrench [®]	SuperSOT [™] -6
DOVE [™]	GTO [™]	MicroPak [™]	QFET [®]	SuperSOT [™] -8
EcoSPARK [™]	HiSeC [™]	MICROWIRE [™]	QS [™]	SyncFET [™]
E ² CMOS [™]	I ² C [™]	MSX [™]	QT Optoelectronics [™]	TinyLogic [®]
EnSigna [™]	i-Lo [™]	MSXPro [™]	Quiet Series [™]	TINYOPTO [™]
FACT [™]	ImpliedDisconnect [™]	OCX [™]	RapidConfigure [™]	TruTranslation [™]
FACT Quiet Series [™]		OCXPro [™]	RapidConnect [™]	UHC [™]
Across the board. Around the world. [™]		OPTOLOGIC [®]	μSerDes [™]	UltraFET [®]
The Power Franchise [®]		OPTOPLANAR [™]	SILENT SWITCHER [®]	UniFET [™]
Programmable Active Droop [™]		PACMAN [™]	SMART START [™]	VCX [™]

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. 115